

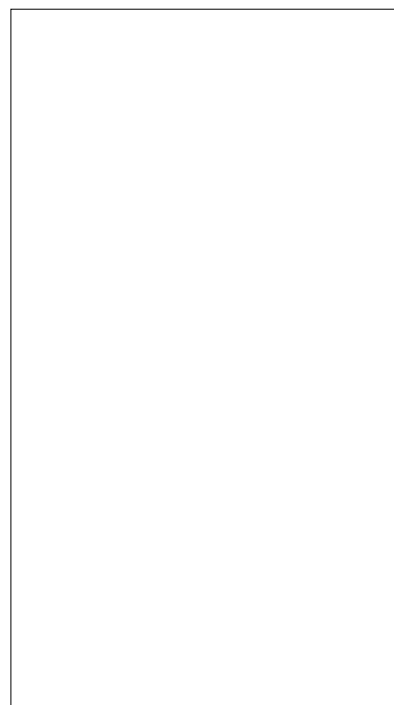


JCT616H 16A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT616H of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-251 is RoHS compliant.



MAIN FEATURES

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	

JCT616H

Average gate power dissipation (T _j =125)	P _{G(AV)}	1	W
Peak gate power	P _{GM}	20	W

ORDERING INFORMATION

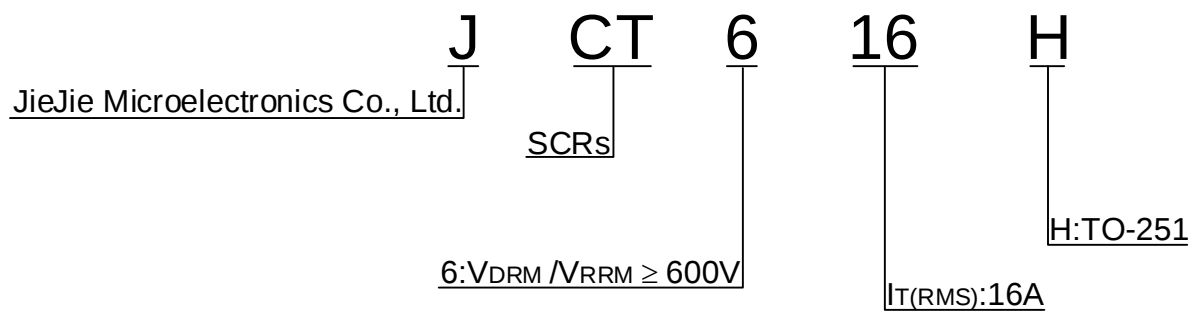


FIG.1: Maximum power dissipation versus RMS on-state current

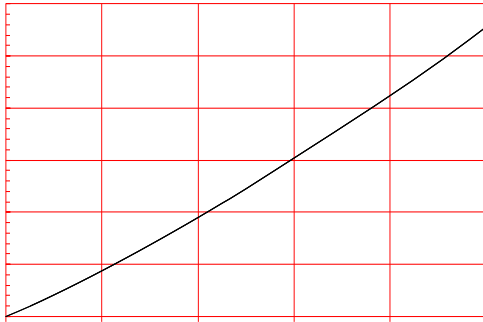
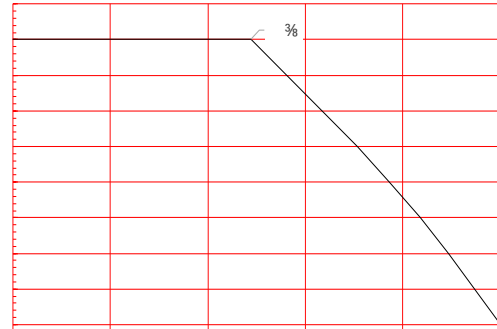


FIG.2: RMS on-state current versus case temperature



ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT616H	600	15	TO-251	80	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A. .0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

JCT616H

JieJie Microelectronics Co., Ltd.